BT148W series

GENERAL DESCRIPTION

Glass passivated, sensitive gate thyristors in a plastic envelope suitable for surface mounting, intended for use in general purpose switching and phase control applications. These devices are intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

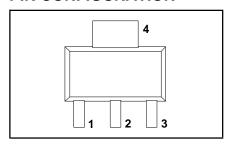
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
V _{DRM} , V _{RRM} I _{T(AV)} I _{T(RMS)} I _{TSM}	BT148W- Repetitive peak off-state voltages Average on-state current RMS on-state current Non-repetitive peak on-state current	400R 400 0.6 1 10	500R 500 0.6 1 10	600R 600 0.6 1 10	V A A A

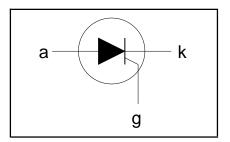
PINNING - SOT223

PIN	DESCRIPTION		
1	cathode		
2	anode		
3	gate		
tab	anode		

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT	
V_{DRM}, V_{RRM}	Repetitive peak off-state voltages		-	-400R 400 ¹	-500R 500 ¹	-600R 600 ¹	>
I _{T(AV)} I _{T(RMS)} I _{TSM}	Average on-state current RMS on-state current Non-repetitive peak on-state current	half sine wave; $T_{sp} \le 112 ^{\circ}\text{C}$ all conduction angles half sine wave; $T_j = 125 ^{\circ}\text{C}$ prior to surge; with reapplied $V_{DRM(max)}$	-		0.6 1		A A
		t = 10 ms t = 8.3 ms	-		10 11		A A
l ² t	I ² t for fusing	t = 10 ms	-		0.5		A ² s
dl _⊤ /dt	Repetitive rate of rise of on-state current after triggering	$I_{TM} = 4 \text{ A}; I_{G} = 200 \text{ mA}; \\ dI_{G}/dt = 200 \text{ mA/}\mu\text{s}$	-		50		A/μs
I _{GM} V _{GM}	Peak gate current		-		1		A
V _{GM}	Peak gate voltage		-		5 5		V
V _{RGM} P _{GM}	Peak reverse gate voltage Peak gate power		_		ວ 1.2		Ŵ
P _{G(AV)}	Average gate power	over any 20 ms period	_		0.12		W
T _{sta}	Storage temperature		-40		150		l °C ∣
T _{stg}	Operating junction temperature		-		125		°C

¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the thyristor may switch to the on-state. The rate of rise of current should not exceed 15 Å/µs.

BT148W series

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th j-sp}	Thermal resistance junction to solder point		-	-	15	K/W
R _{th i-a}	Thermal resistance	pcb mounted, minimum footprint pcb mounted, pad area as in fig:14	- -	156 70	-	K/W K/W

STATIC CHARACTERISTICS

 $T_j = 25$ °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{GT}	Gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$	-	50	200	μΑ
l IĽ	Latching current	$V_{\rm D} = 12 \text{ V}; I_{\rm GT} = 0.1 \text{ A}$	-	0.17	10	mΑ
I _H	Holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$	-	0.10	6	mΑ
Ϊ́Τ	On-state voltage	$I_T = 2 A$	-	1.3	1.5	V
V _{GT}	Gate trigger voltage	$\dot{V}_{D} = 12 \text{ V}; I_{T} = 0.1 \text{ A}$	-	0.4	1.5	V
		$V_R = V_{RRM(max)}$; $I_T = 0.1 \text{ A}$; $T_j = 125 ^{\circ}\text{C}$	0.25	0.3	-	V
I_D, I_R	Off-state leakage current	$V_D = V_{DRM(max)}$; $V_R = V_{RRM(max)}$; $T_j = 125$ °C	-	0.1	0.5	mA

DYNAMIC CHARACTERISTICS

 $T_i = 25$ °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV _D /dt	Critical rate of rise of off-state voltage	V_{DM} = 67% $V_{DRM(max)}$; T_j = 125 °C; exponential waveform; R_{GK} = 100 Ω	-	50	-	V/μs
t _{gt}	Gate controlled turn-on time	$I_{TM} = 4 \text{ A}; V_D = V_{DRM(max)}; I_G = 5 \text{ mA};$ $dI_C/dt = 0.2 \text{ A/us}$	-	2	-	μs
t _q	Circuit commutated turn-off time	$V_D = 67\% V_{DRM(max)}$; $T_j = 125$ °C; $I_{TM} = 2$ A; $V_R = 35$ V; $dI_{TM}/dt = 30$ A/ μ s; $dV_D/dt = 2$ V/ μ s; $R_{GK} = 1$ k Ω	-	100	-	μs

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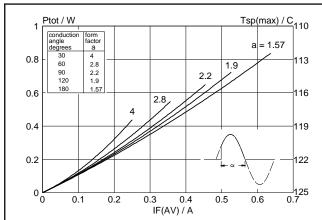


Fig.1. Maximum on-state dissipation, P_{tot} , versus average on-state current, $I_{T(AV)}$, where $a = form \ factor = I_{T(RMS)} / I_{T(AV)}$.

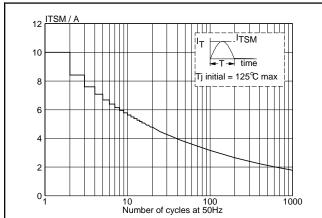


Fig.4. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus number of cycles, for sinusoidal currents, f = 50 Hz.

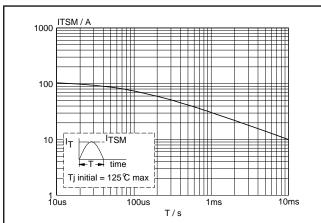


Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus pulse width t_p , for sinusoidal currents, $t_p \le 10$ ms.

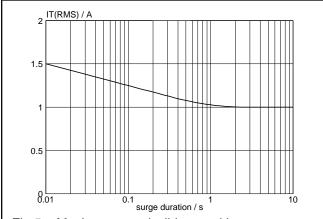


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, f = 50 Hz; $T_{sp} \le 112$ °C.

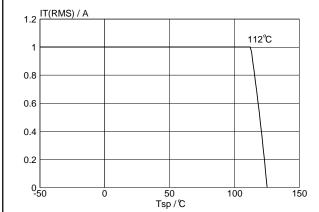
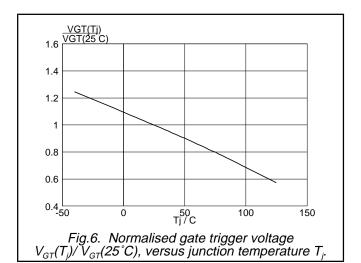
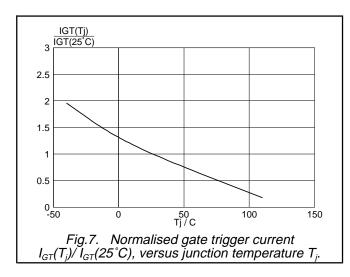
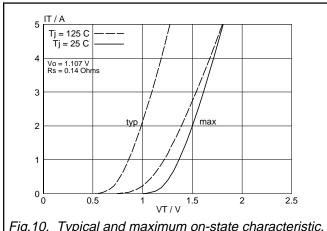


Fig.3. Maximum permissible rms current $I_{T(RMS)}$, versus solder point temperature T_{sp} .



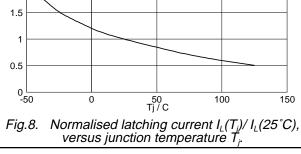
BT148W series

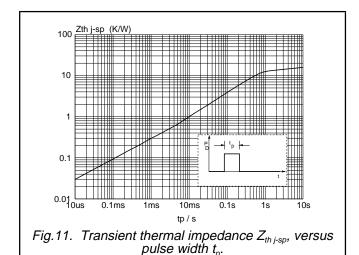


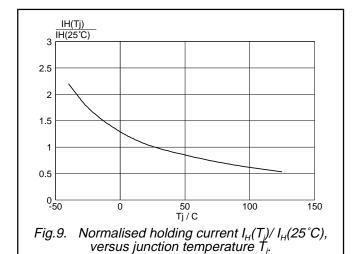


IL(Tj) IL(25°C) 2.5 2 1 0.5

Fig. 10. Typical and maximum on-state characteristic.







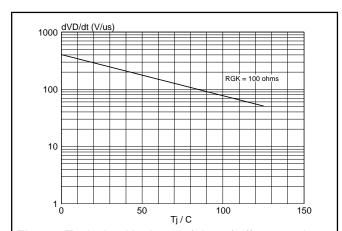
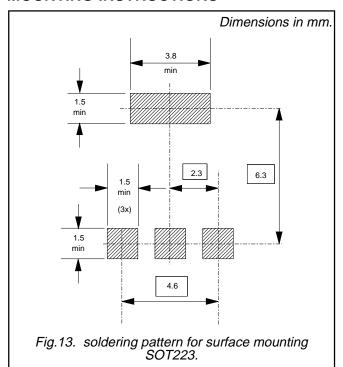


Fig.12. Typical, critical rate of rise of off-state voltage, dV_D/dt versus junction temperature $T_{j\cdot}$

BT148W series

MOUNTING INSTRUCTIONS



PRINTED CIRCUIT BOARD

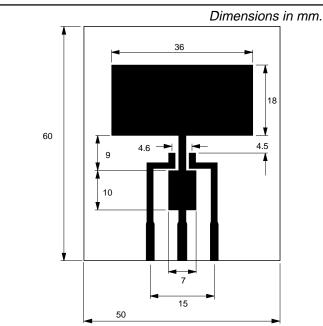
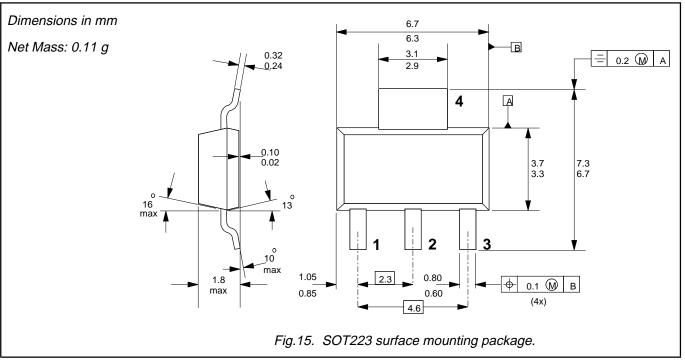


Fig.14. PCB for thermal resistance and power rating for SOT223.

PCB: FR4 epoxy glass (1.6 mm thick), copper laminate (35 µm thick).

BT148W series

MECHANICAL DATA



- Notes
 1. For further information, refer to surface mounting instructions for SOT223 envelope.
 2. Epoxy meets UL94 V0 at 1/8".

Philips Semiconductors Product specification

Thyristors	BT148W series
logic level	

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Product specification	This data sheet contains final product specifications.

Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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